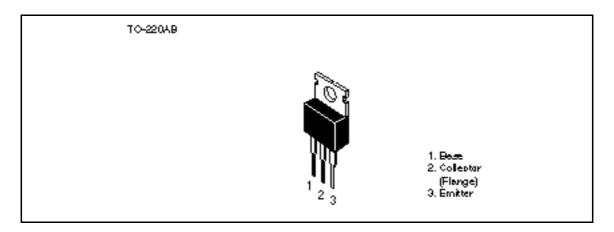
Silicon NPN Triple Diffused

HITACHI

Application

High voltage, high speed and high power switching

Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	500	V
Collector to emitter voltage	V _{CEO}	400	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I _c	3	A
Collector peak current	I _{C(peak)}	6	A
Base current	I _B	1.5	A
Collector power dissipation	P _c *1	30	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

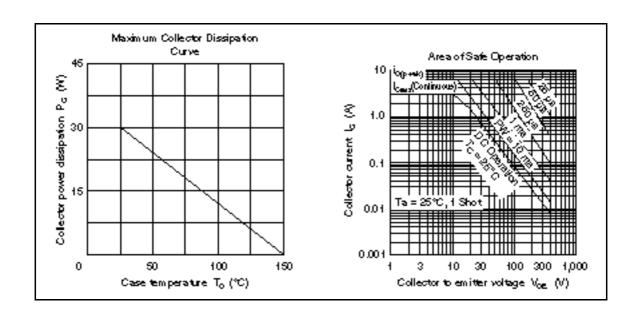
Note: 1. Value at $T_c = 25$ °C.

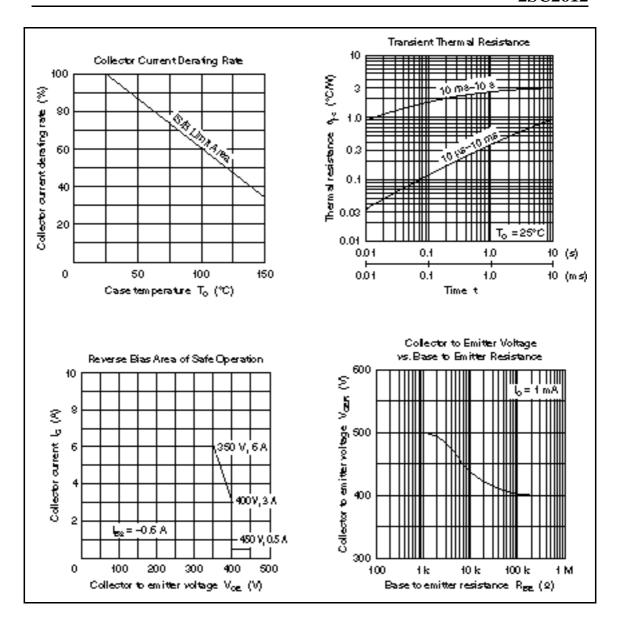


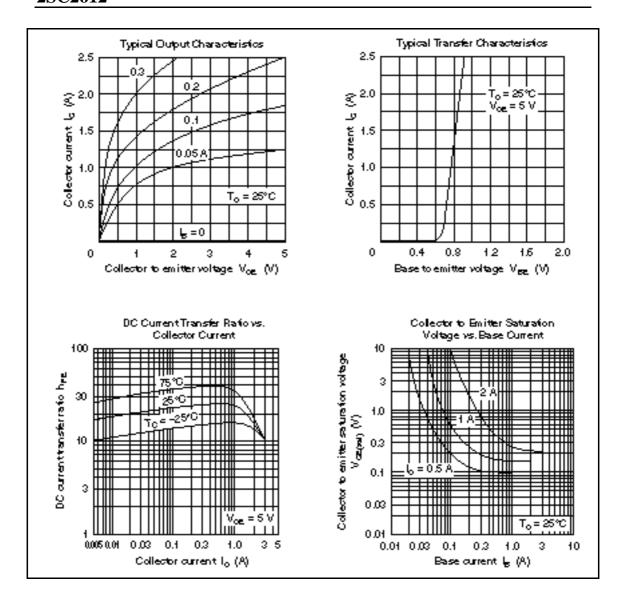
Electrical Characteristics ($Ta = 25^{\circ}C$)

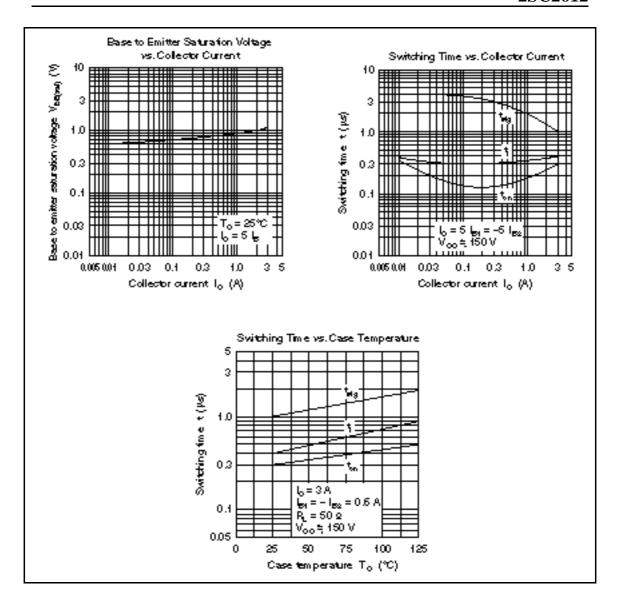
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter sustain voltage	$V_{\text{CEO(sus)}}$	400	_	_	V	$I_{C} = 0.2 \text{ A}, R_{BE} = ,$ L = 100 mH
	V _{CEX(sus)}	400	_	_	V	$I_C = 3 \text{ A}, I_{B1} = -I_{B2} = 0.6 \text{ A}$ $V_{BE} = -5 \text{ V}, L = 180 \mu\text{H},$ Clamped
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	_	_	V	$I_{\rm E} = 10 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	100	μΑ	$V_{CB} = 400 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	100	μΑ	$V_{CE} = 350 \text{ V}, R_{BE} =$
DC current transfer ratio	h _{FE1}	15	_			$V_{CE} = 5 \text{ V}, I_{C} = 1.5 \text{ A}^{*1}$
	h _{FE2}	7	_	_		$V_{CE} = 5 \text{ V}, I_{C} = 3.0 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.0	V	$I_{\rm C} = 1.5 \text{ A}, I_{\rm B} = 0.3 \text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	1.5	V	$I_{\rm C} = 1.5 \text{ A}, I_{\rm B} = 0.3 \text{ A}^{*1}$
Turn on time	t _{on}	_	_	1.0	μs	$I_C = 3 \text{ A}, I_{B1} = -I_{B2} = 0.6 \text{ A},$
Storage time	t_{stg}	_	1.2	2.5	μs	V _{cc} 150 V
Fall time	t _f			1.0	μs	

Note: 1. Pulse test









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